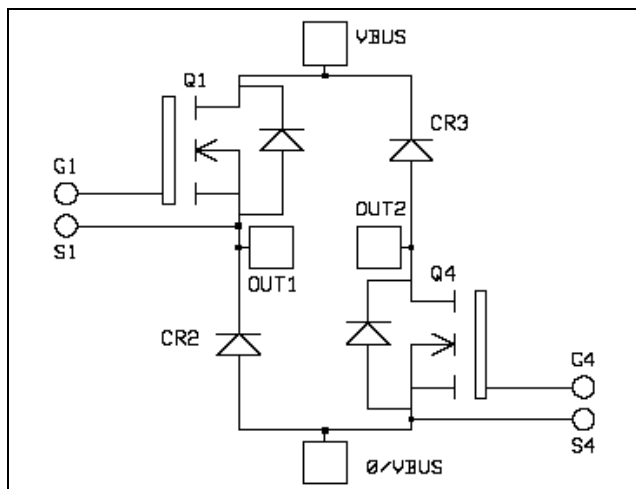


Asymmetrical - bridge MOSFET Power Module

$$V_{DSS} = 200V$$

$$R_{DSon} = 8m\Omega \text{ max @ } T_j = 25^{\circ}C$$

$$I_D = 208A \text{ @ } T_c = 25^{\circ}C$$



Application

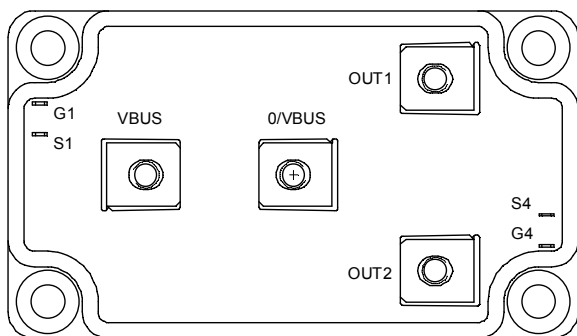
- Welding converters
- Switched Mode Power Supplies
- Switched Reluctance Motor Drives

Features

- Power MOS 7[®] MOSFETs
 - Low R_{DSon}
 - Low input and Miller capacitance
 - Low gate charge
 - Avalanche energy rated
 - Very rugged
- Kelvin source for easy drive
- Very low stray inductance
 - Symmetrical design
 - M5 power connectors
- High level of integration

Benefits

- Outstanding performance at high frequency operation
- Direct mounting to heatsink (isolated package)
- Low junction to case thermal resistance
- Low profile



Absolute maximum ratings

Symbol	Parameter	Max ratings	Unit
V_{DSS}	Drain - Source Breakdown Voltage	200	V
I_D	Continuous Drain Current	$T_c = 25^{\circ}C$	A
		$T_c = 80^{\circ}C$	
I_{DM}	Pulsed Drain current	832	
V_{GS}	Gate - Source Voltage	± 30	V
R_{DSon}	Drain - Source ON Resistance	8	m Ω
P_D	Maximum Power Dissipation	$T_c = 25^{\circ}C$	W
I_{AR}	Avalanche current (repetitive and non repetitive)	100	A
E_{AR}	Repetitive Avalanche Energy	50	mJ
E_{AS}	Single Pulse Avalanche Energy	3000	

CAUTION: These Devices are sensitive to Electrostatic Discharge. Proper Handling Procedures Should Be Followed.

All ratings @ $T_j = 25^\circ\text{C}$ unless otherwise specified

Electrical Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
BV_{DSS}	Drain - Source Breakdown Voltage	$V_{GS} = 0V, I_D = 375\mu A$	200			V
I_{DSS}	Zero Gate Voltage Drain Current	$V_{GS} = 0V, V_{DS} = 200V, T_j = 25^\circ\text{C}$			150	μA
		$V_{GS} = 0V, V_{DS} = 160V, T_j = 125^\circ\text{C}$			750	
$R_{DS(on)}$	Drain - Source on Resistance	$V_{GS} = 10V, I_D = 104A$			8	$m\Omega$
$V_{GS(th)}$	Gate Threshold Voltage	$V_{GS} = V_{DS}, I_D = 5mA$	3		5	V
I_{GSS}	Gate - Source Leakage Current	$V_{GS} = \pm 30V, V_{DS} = 0V$			± 150	nA

Dynamic Characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
C_{iss}	Input Capacitance	$V_{GS} = 0V$		14.4		nF
C_{oss}	Output Capacitance	$V_{DS} = 25V$		4.66		
C_{rss}	Reverse Transfer Capacitance	$f = 1MHz$		0.30		
Q_g	Total gate Charge	$V_{GS} = 10V$		280		nC
Q_{gs}	Gate - Source Charge	$V_{Bus} = 100V$		106		
Q_{gd}	Gate - Drain Charge	$I_D = 208A$		134		
$T_{d(on)}$	Turn-on Delay Time	Inductive switching @ 125°C $V_{GS} = 15V$ $V_{Bus} = 133V$ $I_D = 208A$ $R_G = 2.5\Omega$		32		ns
T_r	Rise Time			64		
$T_{d(off)}$	Turn-off Delay Time			88		
T_f	Fall Time			116		
E_{on}	Turn-on Switching Energy ❶	Inductive switching @ 25°C $V_{GS} = 15V, V_{Bus} = 133V$ $I_D = 208A, R_G = 2.5\Omega$		1698		μJ
E_{off}	Turn-off Switching Energy ❷			1858		
E_{on}	Turn-on Switching Energy ❶	Inductive switching @ 125°C $V_{GS} = 15V, V_{Bus} = 133V$ $I_D = 208A, R_G = 2.5\Omega$		1872		μJ
E_{off}	Turn-off Switching Energy ❷			1972		

Diode ratings and characteristics

Symbol	Characteristic	Test Conditions	Min	Typ	Max	Unit
$I_{F(AV)}$	Maximum Average Forward Current	50% duty cycle $T_c = 75^\circ\text{C}$		200		A
V_F	Diode Forward Voltage	$I_F = 200A$		1	1.1	V
		$I_F = 400A$		1.4		
		$I_F = 200A, T_j = 125^\circ\text{C}$		0.9		
t_{rr}	Reverse Recovery Time	$I_F = 200A, V_R = 133V, di/dt = 400A/\mu s, T_j = 25^\circ\text{C}$		60		ns
		$T_j = 125^\circ\text{C}$		110		
Q_{rr}	Reverse Recovery Charge	$I_F = 200A, V_R = 133V, di/dt = 400A/\mu s, T_j = 25^\circ\text{C}$		400		nC
		$T_j = 125^\circ\text{C}$		1680		

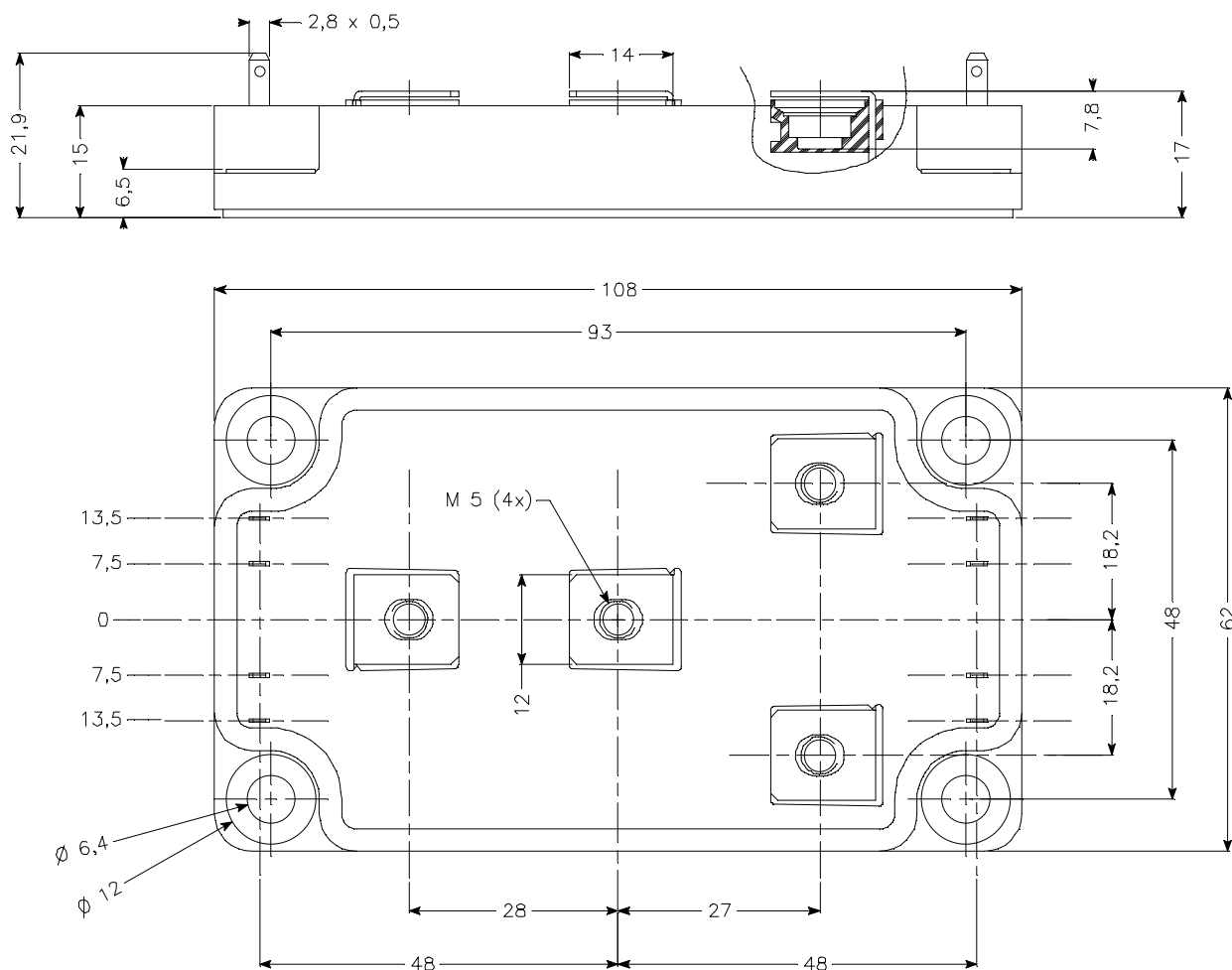
❶ E_{on} includes diode reverse recovery.

❷ In accordance with JEDEC standard JESD24-1.

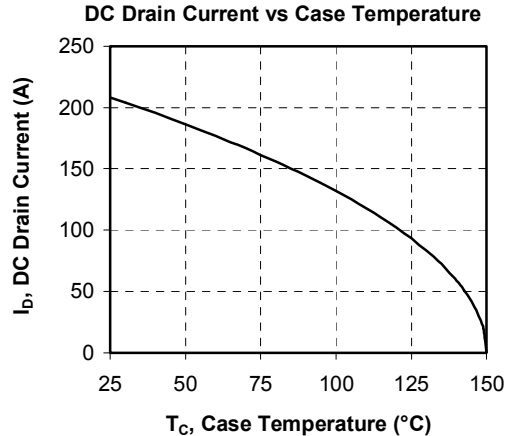
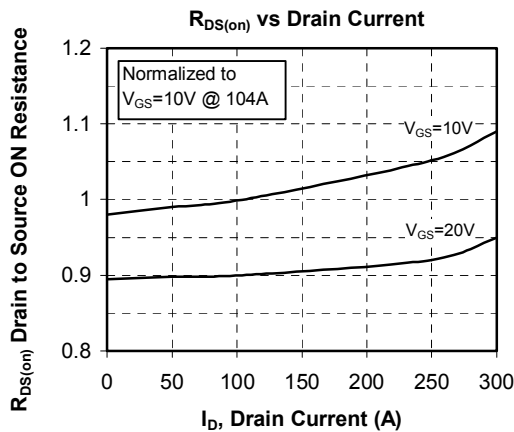
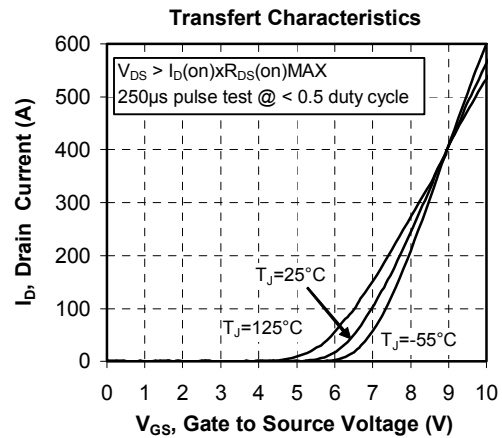
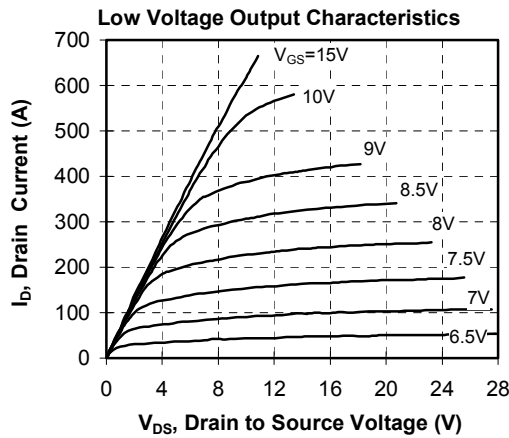
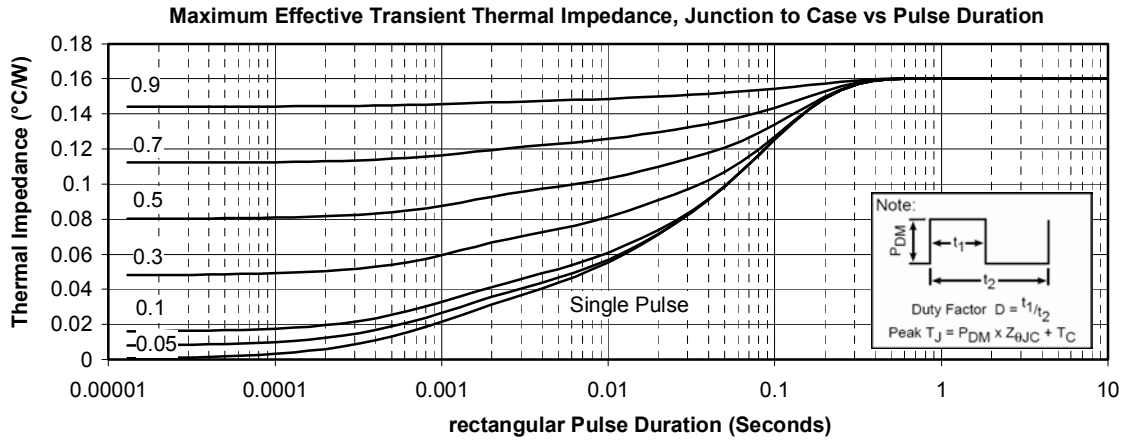
Thermal and package characteristics

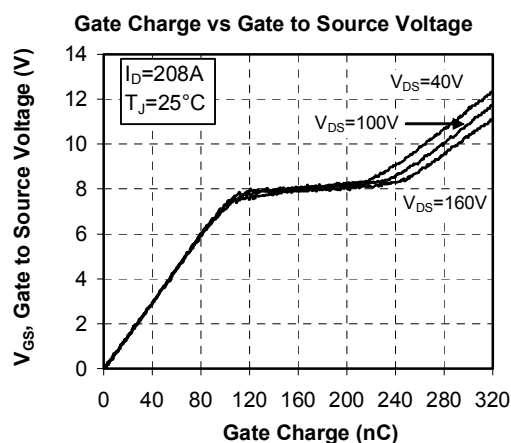
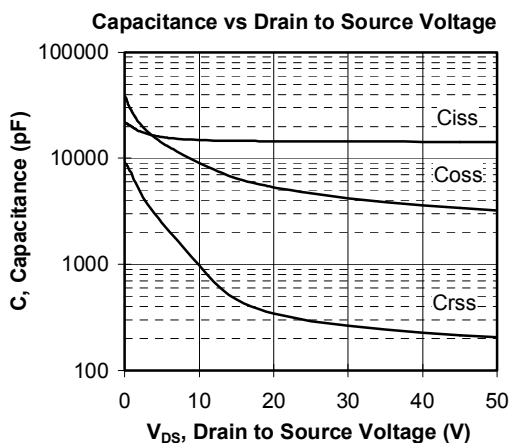
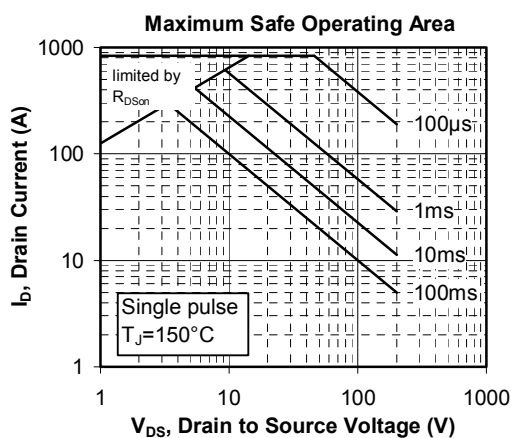
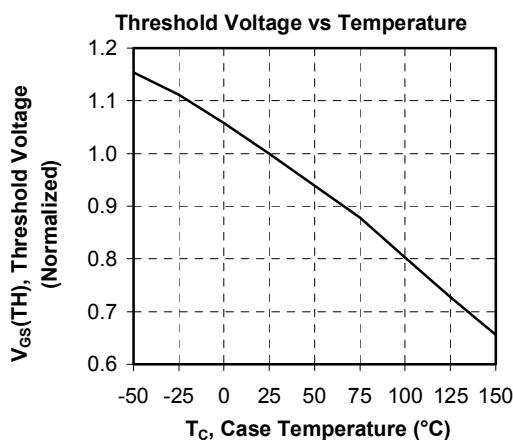
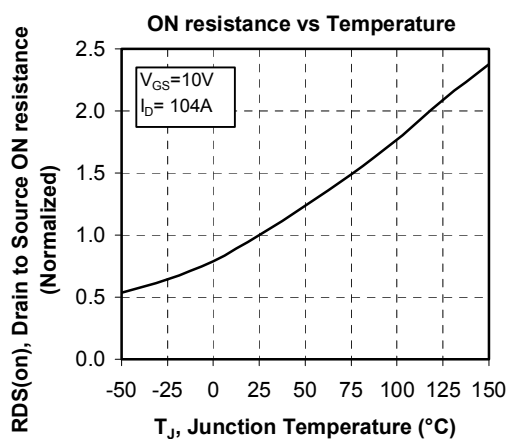
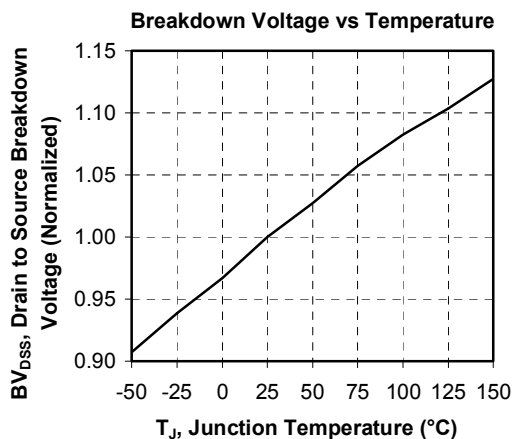
Symbol	Characteristic			Min	Typ	Max	Unit
R _{thJC}	Junction to Case		Transistor			0.16	°C/W
			Diode			0.32	
V _{ISOL}	RMS Isolation Voltage, any terminal to case t =1 min, I isol<1mA, 50/60Hz			2500			V
T _J	Operating junction temperature range			-40		150	°C
T _{STG}	Storage Temperature Range			-40		125	
T _C	Operating Case Temperature			-40		100	
Torque	Mounting torque	To heatsink	M6	3		5	N.m
		For terminals	M5	2		3.5	
Wt	Package Weight					280	g

Package outline

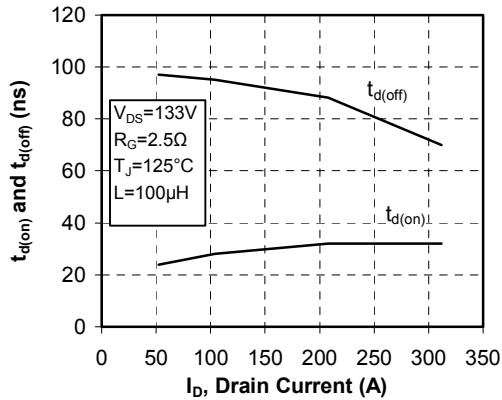


Typical Performance Curve

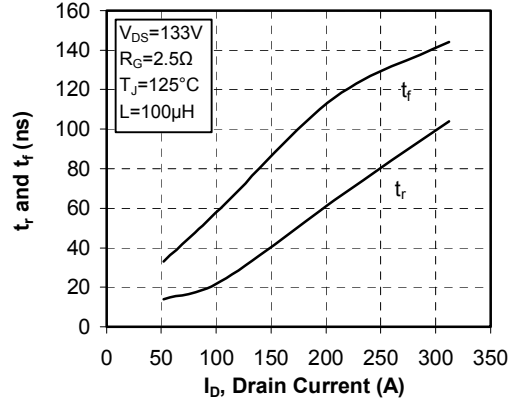




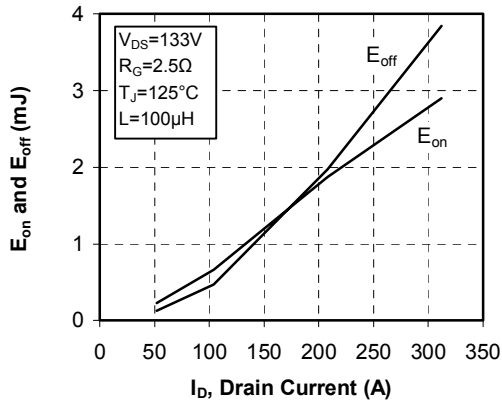
Delay Times vs Current



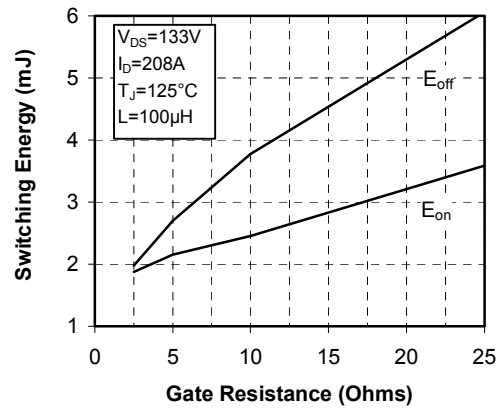
Rise and Fall times vs Current



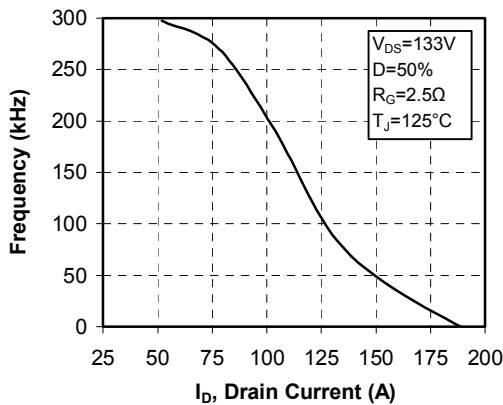
Switching Energy vs Current



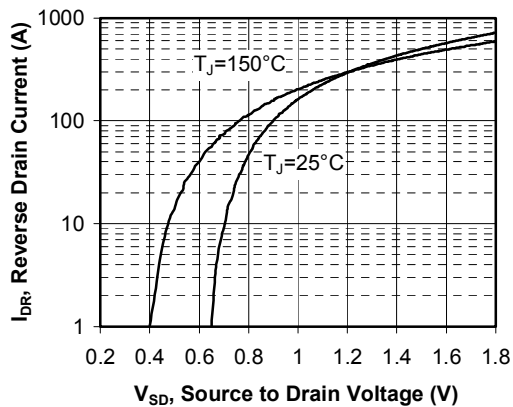
Switching Energy vs Gate Resistance



Operating Frequency vs Drain Current



Source to Drain Diode Forward Voltage



APT reserves the right to change, without notice, the specifications and information contained herein

APT's products are covered by one or more of U.S. patents 4,895,810 5,045,903 5,089,434 5,182,234 5,019,522 5,262,336 6,503,786 5,256,583 4,748,103 5,283,202 5,231,474 5,434,095 5,528,058 and foreign patents. U.S. and Foreign patents pending. All Rights Reserved.